JMD200KD18T2W

Diode Module

Features

- A package of series of two diodes
- Heat transfer through alumina ceramic and metal substrate
- Welding by vacuum welding technology, which provide high reliability

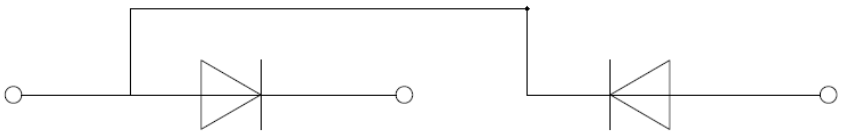
Product Summary

Parameter	Value	Unit
V_{RRM}	1800	V
$I_{F(AV)}$(@ T_C = 100)	200	A
I_{FSM}(@ t_P = 10ms)	5800	A
V_F(Max)	1.60	V

Applications

- AC converter
- Inverter
- DC moto





Absolute Maximum Ratings (@ T_C = 25°C unless otherwise specified)

Parameter	Conditions	Symbol	Values	Unit
Repetitive peak reverse voltage	T_{vj} = 25°C	V_{RRM}	1800	V
Non-repetitive peak reverse voltage	T_{vj} = 25°C	V_{RSM}	1900	V
Average forward current	T_C = 100°C	$I_{F(AV)}$	200	A
Forward surge current	1/2 cycle, Sine wave, 50Hz T_{vj} = 25	I_{FSM}	5800	A
I^2t value for fusing		I^2t	168200	A^2s
RMS isolation voltage	A.C 50Hz(1s/1min)	V_{ISO}	3600/3000	V
Junction temperature range		T_J	-40 ~ +150	
Storage temperature range		T_{stg}	-40 ~ +125	

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Electrical Characteristics (@ T_C = 25°C unless otherwise specified)

Parameter	Conditions	Symbol	Values	Unit

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Typical Electrical & Thermal Characteristics

FIG.1: Forward characteristics(per diode)

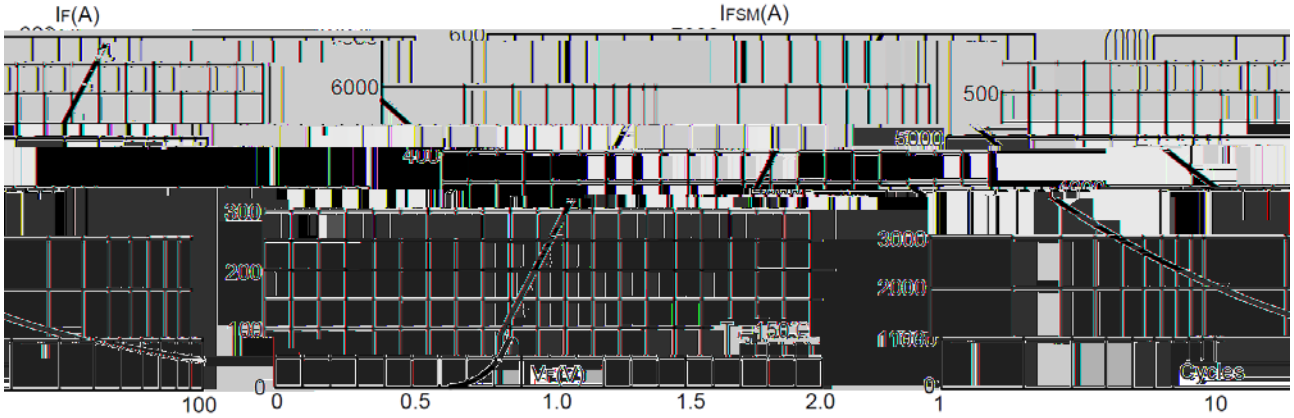
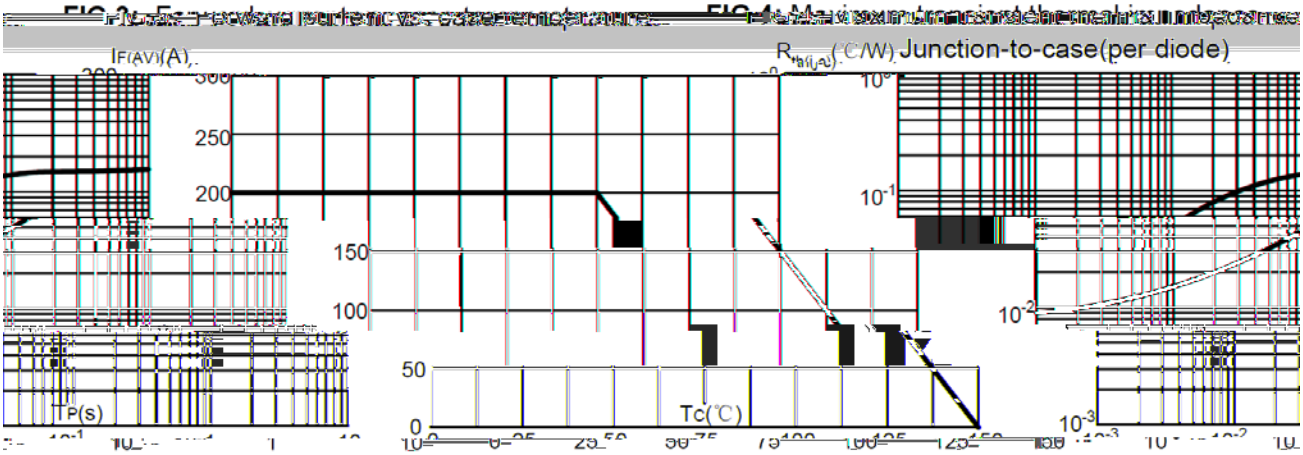
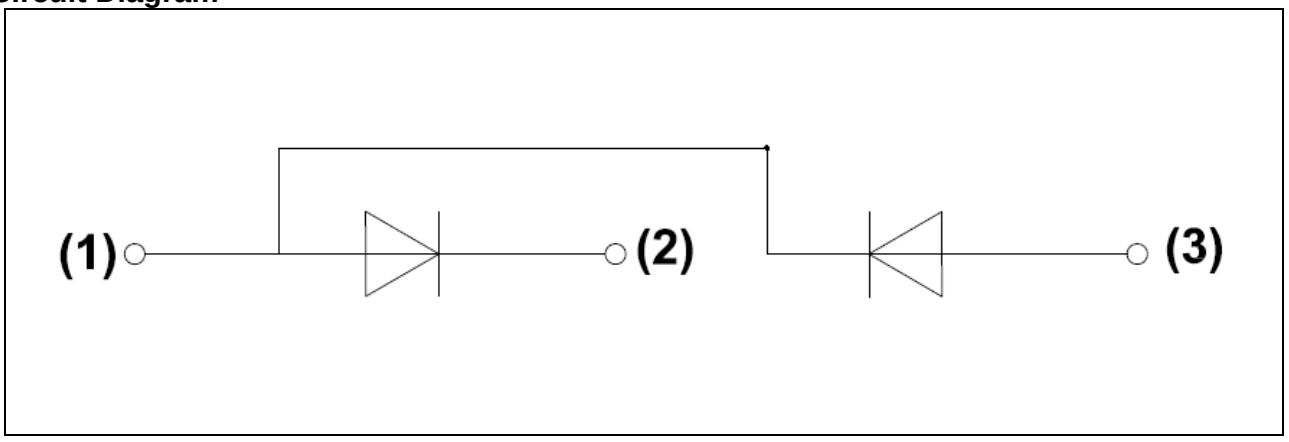


FIG.2: Peak on-state surge current

IFSM(A)



Circuit Diagram



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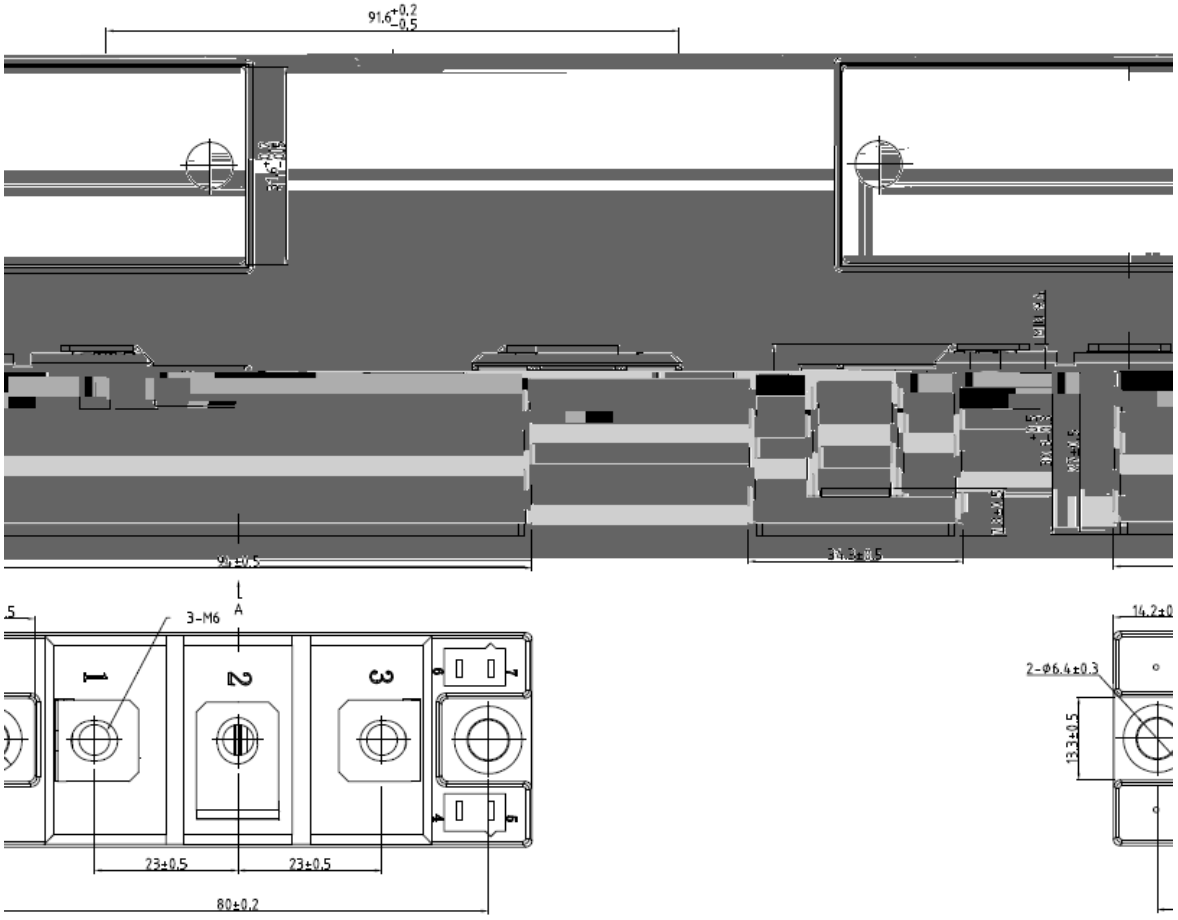
Package Outlines (mm)



Unit of measurement: mm

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